

Dual P-Channel MOSFET, 2.3 A, 20 V HEXFET, 8-Pin SOIC Infineon

Manufacturers	Infineon Technologies Corporation
Package/Case	SOIC-8
Product Type	Transistors
RoHS	Green
Lifecycle	



Images are for reference only

Please submit RFQ for IRF7104PBF or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

Fourth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

- Advanced Process Technology
- Ultra Low On-Resistance
- Dual P-Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- Dynamic dv/dt Rating
- Fast Switching

Features

RoHS Compliant

Low RDS(on)

Dynamic dv/dt Rating

Fast Switching

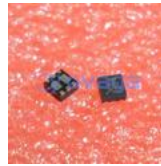
Dual P-Channel MOSFET

Related Products



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Infineon Technologies Corporation
TSOP-6



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PQFN2x2DD



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